GHz TECHNOLOGY
RF·MICROWAVE SILICON POWER TRANSISTORS

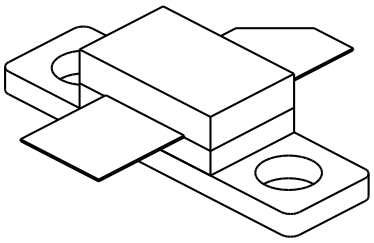
1920AB25

25 Watts, 25 Volts, Class AB
Personal 1930 - 1990 MHz

GENERAL DESCRIPTION

The 1920AB25 is a COMMON EMITTER transistor capable of providing 25 Watts of Class AB, RF output power over the band 1930-1990 MHz. This transistor is specifically designed for **PERSONAL COMMUNICATIONS BASE STATION** amplifier applications. It includes Input prematching and utilizes Gold metalization and HIGH VALUE EMITTER ballasting to provide high reliability and supreme ruggedness. .

CASE OUTLINE
55CX, STYLE 2
COMMON EMITTER



ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25ºC	87 Watts
Maximum Voltage and Current	
BVces Collector to Emitter Voltage	60 Volts
LVceo Collector to Emitter Voltage	27 Volts
BVebo Emitter to Base Voltage	3.5 Volts
Ic Collector Current	10.0 Amps
Maximum Temperatures	
Storage Temperature	- 65 to + 150ºC
Operating Junction Temperature	+ 200ºC

ELECTRICAL CHARACTERISTICS @ 25 ^{O}C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout	Power Out	F =1990 MHz	25			Watt
Pin	Power Input	Vce = 25 Volts			4.0	Watt
Pg	Power Gain	Icq = 0.27 Amps	8.0	9.0		dB
η_c	Collector Efficiency	As Above		43		%
VSWR$_1$	Load Mismatch Tolerance				3:1	

BVces	Collector to Emitter Breakdown	Ic = 50 mA	60			Volts
LVceo	Collector to Emitter Breakdown	Ic = 50 mA	27			Volts
BVebo	Emitter to Base Breakdown	Ie = 10 mA	3.5			Volts
Ices	Collector Leakage Current	Vce = 27 Volts			10	mA
h_{FE}	DC - Current Gain	Vce = 5 V, Ic = 0.7 A	20		100	
Cob	Output Capacitance	F =1 MHz, Vcb = 28 V		28		pF
θ_{jc}	Thermal Resistance	Tc = 25ºC			2.0	ºC/W

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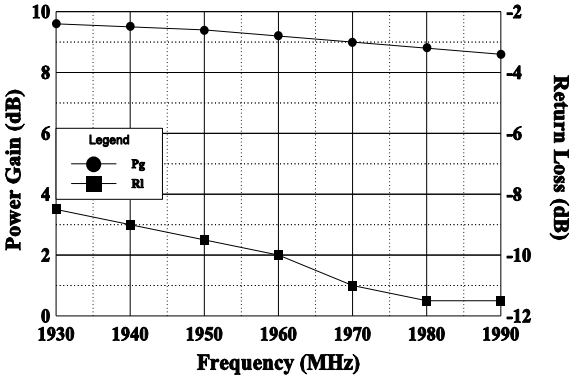
Typical Performance

1920AB25

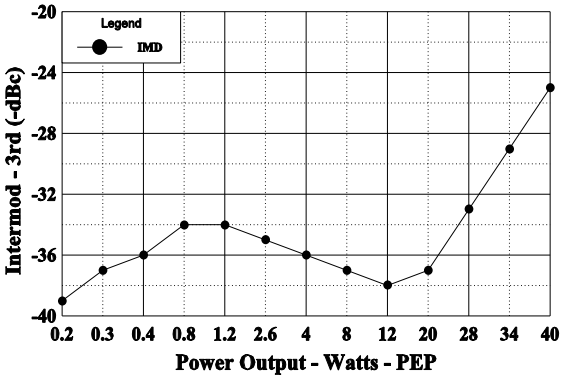
BROADBAND POWER GAIN & RETURN LOSS

Pout = 25 Watts, Vcc = 25 Volts



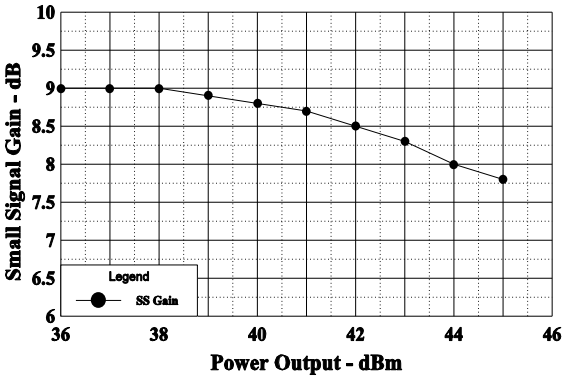
THIRD ORDER IMD vs POWER OUTPUT

Vcc = 25 V, Icq = 200 mA, f = 1990 MHz



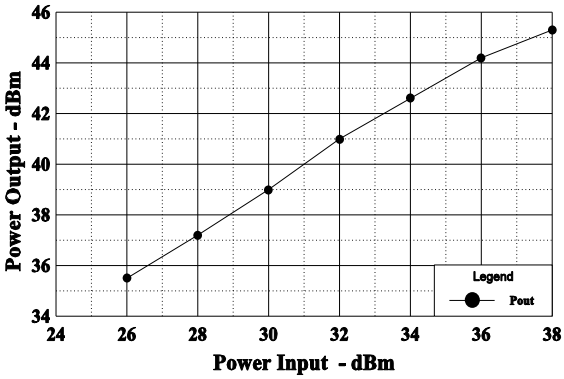
Power Gain vs Power Output

Vcc = 25 V, f = 1990 MHz, Icq = 200mA



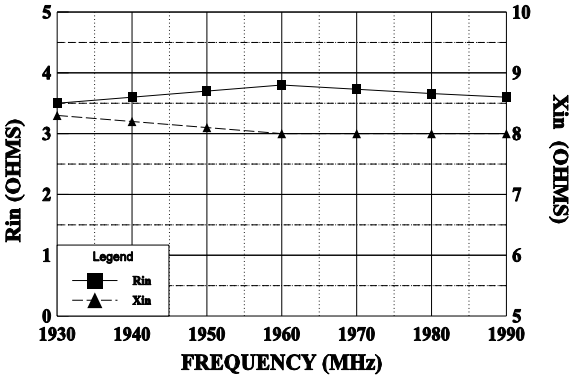
Power Output vs Power Input - dBm

Vcc = 25 V, f = 1990 MHz, Icq = 200mA



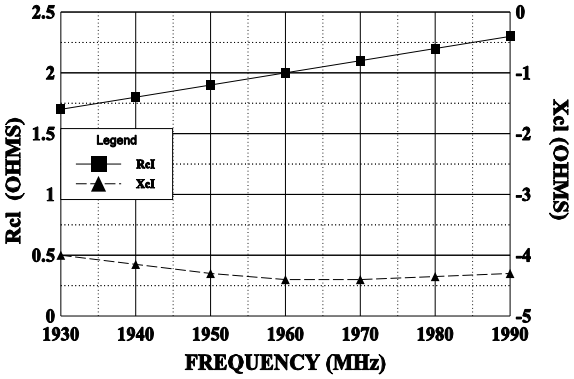
INPUT IMPEDANCE

Vcc = 25 V, Pout = 25 W



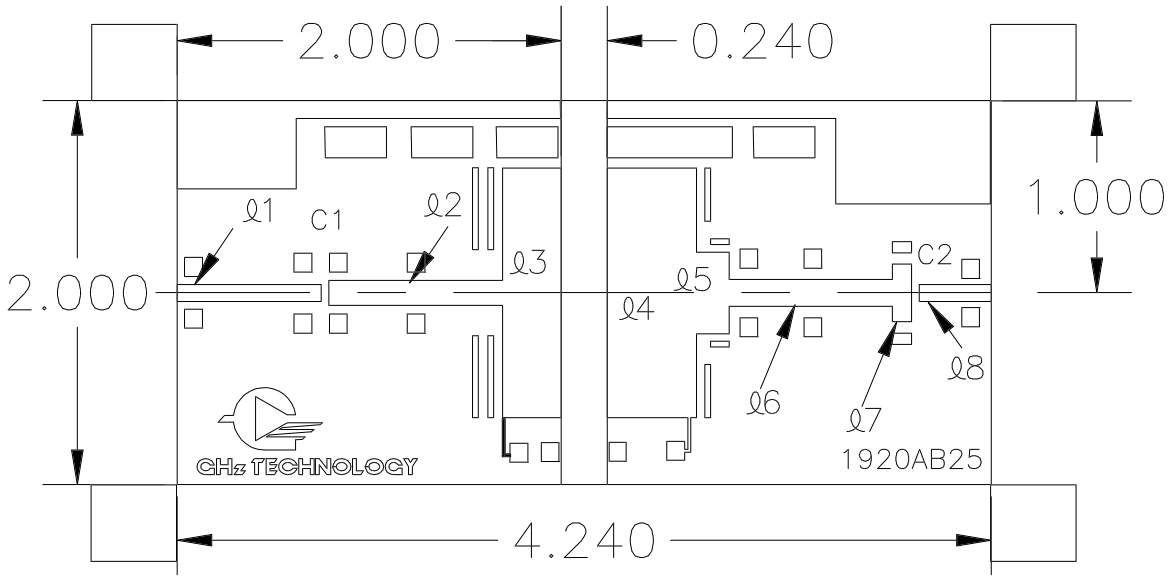
LOAD IMPEDANCE

Vcc = 25 V, Pout= 25 W



August 1996

REVISIONS				
ZONE	REV	DESCRIPTION	DATE	APPROVED



ℓ NO.	X DIM	Y DIM
1	.750	.089
2	.905	.130
3	.305	1.300
4	.465	1.300
5	.170	.425
6	.850	.140
7	.100	.300
8	.375	.089

C1,C2=100pf ATC
1/32" PTFE glass Er=2.5

DATE: 28 AUG 95

GHz TECHNOLOGY	CAGE 0PJR2	DWG NO. 1920AB25	REV 2
		SCALE 1/1	SHEET